RT1P137P

TRANSISTOR WITH RESISTOR FOR SWITCHING APPLICATION SILICON PNP EPITAXIAL TYPE

DESCRIPTION

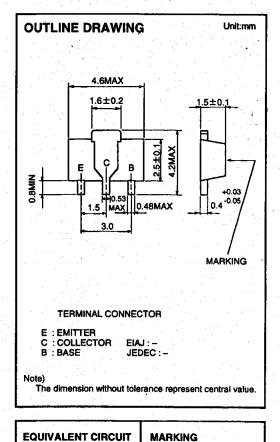
RT1P137P is a one chip transistor with built-in bias resistor, NPN type is RT1N137P.

FEATURE

- Built-in bias resistor (R₁=1kΩ,R₂=22kΩ)
- High collector current Ic=-1A
- ●Low VCE(sat) = -0.3Vmax (@IC=-300mA,IB=-3mA)
- ●High collector dissipation Pc=500mW

APPLICATION

Inverted circuit, switching circuit, interface circuit, driver circuit.



COUT MAXIMUM RATINGS (Ta=25°C) (GND) LOT No

Symbol	Parameter	Ratings	Unit
Vсво	Collector to Base voltage	-40	V
VEBO	Emitter to Base voltage	-6	V
VCEO	Collector to Emitter voltage	-40	V
lc	Collector current	-1	A
Ісм	Peak Collector current	-2	Α
Pc	Collector dissipation(Ta=25°C)	500	mW
Tj	Junction temperature	+150	. °C
Tatg	Storage temperature	-55 to +150	. °C

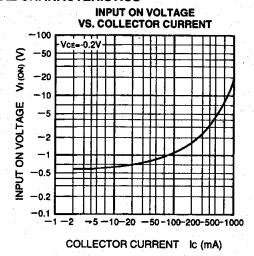
ELECTRICAL CHARACTERISTICS (Ta=25°C)

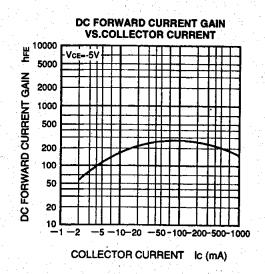
Symbol	Parameter	Test conditions	Limits			Unit
	i dialietei	rest conditions		Тур	Max	Othe
V(BR)CEO	C to E break down voltage	Ic=-1mA,RBE=∞	-40			V
Ісво	Collector cut off current	Vcb=-40V,IE=0			-0.1	μА
hfe	DC forward current gain	VcE=-5V,lc=-100mA	100			
VCE(sat)	C to E saturation voltage	ic=-300mA,is=-3mA		-0.1	-0.3	V
VI(ON)	Input on voltage	VcE=-0.2V,lc=-300mA		-2.4	-4.0	V
VI(OFF)	Input off voltage	VCE=-5V,IC=-100 μ A	0.4	0.53		٧
Ri	Input resistor		0.7	1.0	1.3	kΩ
R2/R1	Resistor ratio		20	22	24	
fτ	Gain band width product	VCE=-6V,IE=10mA		130		MHz

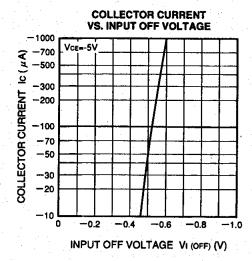
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TYPICAL CHARACTERISTICS









http://www.idc-com.co.jp 6-41, TSUKUBA, ISAHAYA, NAGASAKI, 854-0065, JAPAN

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